Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application. Claims 9, 19 and 28 are herein canceled without prejudice.

Listing of Claims:

1. (Currently amended) A method of forming a nitrogen-containing dielectric film comprising:

incorporating nitrogen into a dielectric film using ammonia (NH_3) gas in a rapid thermal annealing process, wherein an ultra-low pressure equal to or less than about 10 Torr is used for the rapid thermal annealing process at a temperature between about 900-1100°C, wherein the nitrogen incorporated into the dielectric film forms only one nitrogen concentration peak, and wherein the nitrogen concentration peak occurs at the top surface of the dielectric film.

2. (Canceled)

3. (Previously presented) The method of forming a nitrogen-containing dielectric film of claim 1 wherein the nitrogen incorporated into the dielectric film has a nitrogen concentration equal to or greater than 5%.

4. (Previously presented) The method of forming a nitrogen-containing dielectric film of claim 1 wherein the dielectric film is equal to or less than about 12 angstroms.

5. (Canceled)

6. (Previously presented) The method of forming a nitrogen-containing dielectric film of claim 1 wherein the dielectric film is silicon dioxide (SiO_2).

7. (Previously presented) The method of forming a nitrogen-containing dielectric film of claim 1 wherein after the nitrogen is incorporated, a silicon oxynitride is formed.

8. (Currently amended) A method of forming a gate stack comprising:

forming a silicon dioxide film on a substrate;

incorporating nitrogen into the silicon dioxide film using a rapid thermal annealing process with ammonia (NH_3) gas at an ultra-low pressure equal to or less than about 10 Torr and at a temperature between about 900-1100°C, the incorporating of nitrogen forming a silicon oxynitride film on the substrate;

continuing the rapid thermal annealing process with ammonia (NH_3) gas for a sufficient amount of time for nitrogen to be incorporated into the silicon dioxide film to

form the silicon oxynitride film with a nitrogen concentration of about or more than 5%, wherein the nitrogen incorporated into the silicon dioxide film forms only one nitrogen concentration peak, and wherein the nitrogen concentration peak occurs at the top surface of the silicon dioxide film; and

forming a cap layer on the silicon oxynitride.

9. (Canceled)

10. (Previously presented) The method of forming a gate stack of claim 8 further comprising:

subjecting the silicon oxynitride film to a post annealing process after the silicon oxynitride is formed, wherein the post annealing process occurs at a temperature between about 1000-1100°C.

11. (Original) The method of forming a gate stack of claim 10 wherein the post annealing process occurs at a pressure of less than or equal to about 5 Torr.

12. (Currently amended) A method of forming a dielectric film comprising:

incorporating nitrogen into a silicon dioxide film using ammonia (NH_3) gas in a rapid thermal annealing process at a temperature between about 900-1100°C, wherein an ultra-low pressure equal to or less than about 10 Torr is used for the rapid thermal

annealing process, the incorporating of nitrogen into the silicon dioxide film forming a silicon oxynitride film, wherein the nitrogen incorporated into the silicon dioxide film forms only one nitrogen concentration peak, and wherein the nitrogen concentration peak occurs at the top surface of the silicon dioxide film; and

post-annealing the silicon oxynitride film after a sufficient amount of nitrogen is incorporated into the silicon dioxide film.

13. (Canceled)

14. (Original) The method of forming a dielectric film of claim 12 wherein the nitrogen incorporated into the silicon dioxide film has a nitrogen concentration equal to or greater than 5%.

15. (Previously presented) The method of forming a dielectric film of claim 12 wherein the silicon dioxide film is equal to or less than about 12 angstroms.

16. (Canceled)

17. (Previously presented) The method of forming a dielectric film of claim 12 further comprising forming the silicon dioxide film.

18. (Currently amended) A method of forming a gate stack comprising:

placing a substrate into a first processing chamber of a cluster tool, the cluster tool having a plurality of processing chambers;

forming a silicon dioxide film on the silicon wafer in the first processing chamber;

without breaking vacuum, transferring the substrate from the first processing chamber into a second processing chamber, the second processing chamber capable of running a rapid thermal annealing process at a reduced pressure equal to or less than about 10 Torr;

introducing ammonia (NH_3) gas into the second processing chamber while maintaining ~~an ultra-low pressure of~~ the second processing chamber at a temperature between about 900-1100°C and at an ultra-low pressure to form a silicon oxynitride film; and

continuing the ammonia (NH_3) gas into the second processing chamber for a sufficient amount of time for nitrogen to be incorporated into the silicon dioxide film to a nitrogen concentration of about or more than 5%, wherein the nitrogen incorporated into the silicon dioxide film forms only one nitrogen concentration peak, and wherein the nitrogen concentration peak occurs at the top surface of the silicon dioxide film.

19. (Canceled)

20. (Previously presented) The method of forming a gate stack of claim 18 comprising:

subjecting the substrate to a post annealing process after the silicon oxynitride film is formed, wherein the post annealing process occurs at a temperature between about 1000-1100°C.

21. (Original) The method of forming a gate stack of claim 20 wherein the post annealing process occurs in a third processing chamber.

22. (Original) The method of forming a gate stack of claim 20 wherein the post annealing process occurs at a pressure of about 5 Torr.

23. (Canceled)

24. (Currently amended) A method of treating a dielectric film comprising:

exposing the dielectric film to ammonia (NH_3) gas at an ultra-low pressure equal to or less than about 10 Torr; and

subjecting the dielectric film to a rapid thermal annealing process during the exposing of the dielectric film to the ammonia (NH_3) gas to incorporate nitrogen into the dielectric film to form a silicon oxynitride film, wherein the rapid thermal annealing process occurs at a temperature between about 900-1100°C, wherein the nitrogen

incorporated into the dielectric film forms only one nitrogen concentration peak, and wherein the nitrogen concentration peak occurs at the top surface of the dielectric film.

25. (Canceled)

26. (Original) The method of treating a dielectric film of claim 24 wherein the dielectric film is silicon dioxide (SiO_2).

27. (Previously presented) The method of treating a dielectric film of claim 24 wherein after the nitrogen is incorporated, a silicon oxynitride film is formed.

28. (Canceled)

29. (Previously presented) The method of treating a dielectric film of claim 27 further comprising:

subjecting the silicon oxynitride film to a post annealing process after the silicon oxynitride film is formed, wherein the post annealing process occurs at a temperature between about 1000-1100°C.

30. (Original) The method of treating a dielectric film of claim 29 wherein the post annealing process occurs at a pressure of less than or equal to about 5 Torr.

31. (Original) The method of treating a dielectric film of claim 24 wherein the subjecting the dielectric film to the rapid thermal annealing process is continued until a concentration of nitrogen of at least about 5% is incorporated into the dielectric film.

32. (Original) The method of treating a dielectric film of claim 27 further comprising subjecting the silicon oxynitride film to a post-annealing process wherein the silicon oxynitride is post annealed in a non-nitridation atmosphere after a desired concentration of nitrogen is incorporated into the dielectric film.

33.-37. (Canceled)

38. (Currently amended) A method of forming a nitrogen-containing dielectric film comprising:

forming a silicon dioxide dielectric film on a substrate; and

incorporating nitrogen into the silicon dioxide dielectric film using a rapid thermal annealing process with ammonia (NH_3) gas at an ultra-low pressure equal to or less than about 10 Torr and at a temperature between about 900-1100°C.

39. (Previously presented) The method of claim 38, wherein the rapid thermal annealing process with ammonia (NH_3) gas converts the silicon dioxide dielectric film to a silicon oxynitride film.

40. (Canceled)

41. (Previously presented) The method of claim 38, wherein the nitrogen incorporated into the silicon dioxide dielectric film forms only one nitrogen concentration peak, and wherein the nitrogen concentration peak occurs at the top surface of the dielectric film.

42. (Previously presented) The method of claim 38, further comprising: continuing the rapid thermal annealing process with ammonia (NH_3) gas for a sufficient amount of time for nitrogen to be incorporated into the silicon dioxide dielectric film with a nitrogen concentration of about or more than 5%.